External_Type	Material_Group	Substances	CAS_Number	Mass	Mass_Percentage_in_Leaf	Massmg
Die		Lead Dioxide (PbO2)	1309-60-0	0.00141	0.74	0.07548
	Doped silicon	Silicon (Si)	7440-21-3	0.1896	99.26	10.12452
			Subtotal	0.19101	100	10.2
Solder Wire	Pure metal	Tin (Sn)	7440-31-5	0.00585	5.0	0.3125
	Pure metal	Silver (Ag)	7440-22-4	0.00176	1.5	0.09375
	Pure metal	Lead (Pb)	7439-92-1	0.10943	93.5	5.84375
			Subtotal	0.11704	100	6.25
Lead Frame		Phosphorous (P)	7723-14-0	0.01891	0.03	1.00983
		Nickel (Ni) - cas no. 7440-02-0	7440-02-0	0.68079	1.08	36.35388
		Copper (Cu)	7440-50-8	62.33647	98.89	3,328.73629
			Subtotal	63.03617	100	NaN
Mould Compound	Polymer	Phenol Formaldehyde resin (generic)	9003-35-4	2.67527	7.7	142.8581
	Polymer	Epichlorohydrin/Diethyleneglycol Epoxy resin (generic)	25928-94-3	4.16925	12.0	222.636
	Filler	Silica fused	60676-86-0	27.79502	80.0	1,484.24
	Carbon Black	Carbon black	1333-86-4	0.10423	0.3	5.5659
			Subtotal	34.74377	100	NaN
Post-plating	Pure metal	Tin (Sn)	7440-31-5	1.79215	100.0	95.7
			Subtotal	1.79215	100	95.7
Wire	Pure metal	Aluminium (Al)	7429-90-5	0.11985	100.0	6.4
			Subtotal	0.11985	100	6.4
			Total	99.99999	100	NaN

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